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## **Thyristor**

 $V_{\mathsf{RRM}}$ 1600 V

30 A

1.42 V

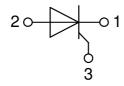
### Single Thyristor

#### Part number

#### **CMA30E1600PB**



Backside: anode



#### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

#### **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### Terms \_Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;
  the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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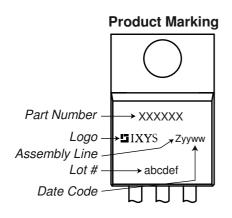


Thyristo				Ì	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Un
V <sub>RSM/DSM</sub>	max. non-repetitive reverse/forwa		$T_{VJ} = 25^{\circ}C$			1700	
V <sub>RRM/DRM</sub>	max. repetitive reverse/forward bl	<u> </u>	$T_{VJ} = 25^{\circ}C$			1600	,
I <sub>R/D</sub>	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			10	μ
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 125^{\circ}C$			2	m
V <sub>T</sub>	forward voltage drop	$I_T = 30 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1.42	,
		$I_T = 60 \text{ A}$				1.80	١
		I <sub>T</sub> = 30 A	$T_{VJ} = 125$ °C			1.42	,
		$I_T = 60 \text{ A}$				1.92	,
I <sub>TAV</sub>	average forward current	T <sub>C</sub> = 115°C	T <sub>vJ</sub> = 150°C			30	1
I <sub>T(RMS)</sub>	RMS forward current	180° sine				47	
V <sub>T0</sub>	threshold voltage		T <sub>v.i</sub> = 150°C			0.90	,
r <sub>T</sub>	slope resistance   for power lo	oss calculation only	***			17	m۵
R <sub>thJC</sub>	thermal resistance junction to cas	e				0.5	K/V
R <sub>thCH</sub>	thermal resistance case to heatsin				0.50		K/V
P <sub>tot</sub>	total power dissipation		T <sub>C</sub> = 25°C		0.00	250	V
I <sub>TSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{V,I} = 45^{\circ}C$			260	
*TSM	max. Torward barge barrers	t = 8.3  ms; (60 Hz), sine	$V_R = 0 V$			280	
		t = 0.5  ms; (60 Hz), sine t = 10  ms; (50 Hz), sine	$V_{R} = 0 V$ $T_{V,I} = 150 ^{\circ}C$			220	,
		. , , , ,	••				į
10.	valva fau fivalia a	t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			240	
l²t	value for fusing	t = 10  ms; (50  Hz),  sine	$T_{VJ} = 45^{\circ}C$			340	A <sup>2</sup>
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			325	A <sup>2</sup>
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			240	A <sup>2</sup>
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			240	A <sup>2</sup>
<b>C</b> J	junction capacitance	$V_R = 400 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		13		pl
$P_{GM}$	max. gate power dissipation	t <sub>P</sub> = 30 μs	$T_{\rm C} = 150 {\rm ^{\circ}C}$			10	۷
		t <sub>P</sub> = 300 μs				5	٧
$P_{GAV}$	average gate power dissipation					0.5	٧
(di/dt) <sub>cr</sub>	critical rate of rise of current	$T_{VJ} = 125 ^{\circ}\text{C}; f = 50 \text{Hz}$ re	epetitive, $I_T = 90 A$			150	Α/μ
		$t_P = 200 \mu s; di_G/dt = 0.2 A/\mu s;$					
		$I_{G} = 0.2 \text{ A}; V = \frac{2}{3} V_{DRM}$ no	on-repet., $I_T = 30 \text{ A}$			500	Α/μ
(dv/dt) <sub>cr</sub>	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125$ °C			500	V/µ
		R <sub>GK</sub> = ∞; method 1 (linear volta	ge rise)				
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 6 V	$T_{VJ} = 25^{\circ}C$			1.3	١
G1			$T_{VJ} = -40$ °C			1.6	١
I <sub>GT</sub>	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 25^{\circ}C$			28	m
•GI	gate trigger carron.	<b>V</b> <sub>D</sub> = <b>0 V</b>	$T_{VJ} = -40$ °C			50	m/
V <sub>GD</sub>	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$			0.2	1117
	gate non-trigger current	V <sub>D</sub> — /3 V <sub>DRM</sub>	1 <sub>VJ</sub> = 130 O			1	į
I <sub>GD</sub>	<u> </u>	10 ue	T 05.00				m
I <sub>L</sub>	latching current	$t_p = 10 \mu\text{s}$	$T_{VJ} = 25^{\circ}C$			90	m
		$I_{G} = 0.2A$ ; $di_{G}/dt = 0.2A/\mu s$					
I <sub>H</sub>	holding current	$V_D = 6 V R_{GK} = \infty$	$T_{VJ} = 25 ^{\circ}\text{C}$			60	m
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25$ °C			2	μ
		$I_G = 0.5 \text{ A}; \text{ di}_G/\text{dt} = 0.5 \text{ A}/\mu\text{s}$					
t <sub>q</sub>	turn-off time	$V_R = 100 \text{ V}; I_T = 30 \text{ A}; V = \frac{2}{3}$	$V_{DRM}$ $T_{VJ} = 125 °C$		150		μ
		$di/dt = 10 A/\mu s dv/dt = 20 V$	/us t = 200 us				1 1 1





Package	Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per terminal			35	Α	
T <sub>VJ</sub>	virtual junction temperature		-40		150	°C	
T <sub>op</sub>	operation temperature		-40		125	°C	
T <sub>stg</sub>	storage temperature		-40		150	°C	
Weight				2		g	
M <sub>D</sub>	mounting torque		0.4		0.6	Nm	
F <sub>c</sub>	mounting force with clip		20		60	N	



#### Part description

C = Thyristor (SCR)

M = Thyristor

A = (up to 1800V)

30 = Current Rating [A]

E = Single Thyristor

1600 = Reverse Voltage [V] PB = TO-220AB (3)

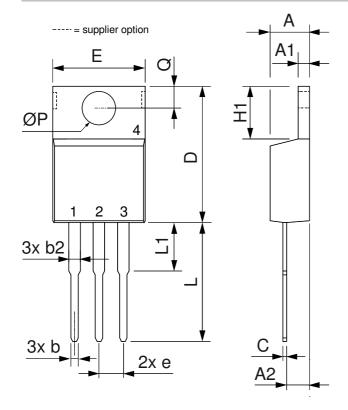
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CMA30E1600PB	CMA30E1600PB	Tube	50	503348

Similar Part	Package	Voltage class
CMA30E1600PN	TO-220ABFP (3)	1600
CMA30E1600PZ	TO-263AB (D2Pak) (2HV)	1600
CLA30E1200PB	TO-220AB (3)	1200
CS22-12io1M	TO-220ABFP (3)	1200
CLA30E1200PC	TO-263AB (D2Pak) (2)	1200
CLA30E1200HB	TO-247AD (3)	1200
CS22-08io1M	TO-220ABFP (3)	800

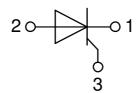
Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	$R_0$	Thyristor		
V <sub>0 max</sub>	threshold voltage	0.9		V
$R_{0 \text{ max}}$	slope resistance *	14		$m\Omega$



### Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
Α	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
С	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125





#### **Thyristor**

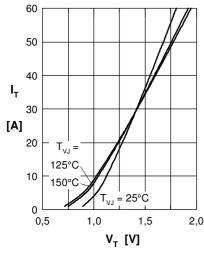


Fig. 1 Forward characteristics

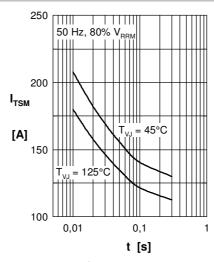


Fig. 2 Surge overload current  $I_{TSM}$ : crest value, t: duration

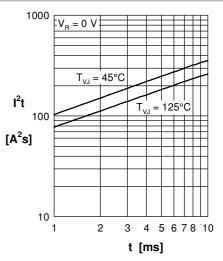


Fig. 3 I<sup>2</sup>t versus time (1-10 s)

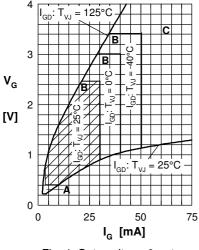


Fig. 4 Gate voltage & gate current Triggering: A = no; B = possible; C = safe

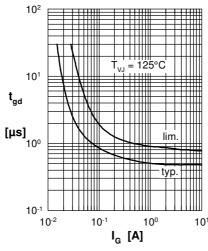


Fig. 5 Gate controlled delay time  $t_{\rm gd}$ 

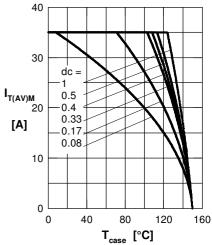


Fig. 6 Max. forward current at case temperature

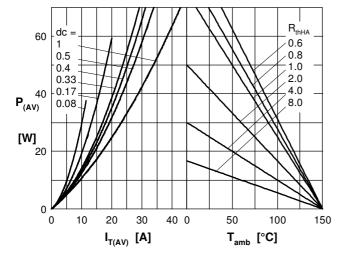


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

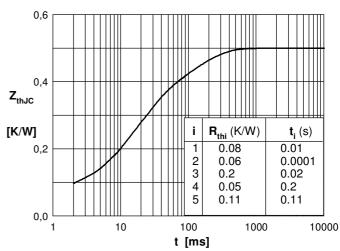


Fig. 7 Transient thermal impedance junction to case